

Fast Thyristor

AT308F

Key Parameters

$I_{TAV(M)}$	=	308	A
V_{DRM}/V_{RRM}	=	200 - 600	V
I_{TSM}	=	4000	A
V_{TO}	=	1	V
r_T	=	0.7	mΩ

Properties

- International standard package
- Metal case with ceramic insulator
- Low on-state and switching losses
- High operation reliability
- Optimum power handling capability

MAXIMUM ALLOWABLE RATINGS

Symbols and parameters			Maximum Limits	Unit
V_{DRM}	Repetitive peak forward voltage	$t_{vj} = -40\text{ °C} \dots t_{vj\text{ max}}$	200	V
V_{RRM}	Repetitive peak reverse voltage		400	V
V_{DSM}	Non-repetitive peak forward off-state voltage	$t_{vj} = -40\text{ °C} \dots t_{vj\text{ max}}$	600	V
V_{RSM}	Non-repetitive peak reverse voltage	$t_{vj} = +25\text{ °C} \dots t_{vj\text{ max}}$	400	V
I_{TAVM}	Average on-state current	$t_c = 85\text{ °C}$ $t_c = 71\text{ °C}$	250 650	V
I_{TRMSM}	RMS on-state current		308 382	A
I_{TSM}	Surge current		600	A
I^2t	I^2t -value	$t_{vj} = 25\text{ °C}, t_p = 10\text{ ms}$ $t_{vj} = t_{vj\text{ max}}, t_p = 10\text{ ms}$	4600 4000	A
$(dv/dt)_{cr}$	Critical rate of rise of off-state voltage	$t_{vj} = t_{vj\text{ max}}$ $V_D = 0.87 V_{DRM}$	106 80	kA ² s kA ² s
			1) B:	50
			2) C*:	50
			L:	500
			M*:	500
$(di/dt)_{cr}$	Critical rate of rise of on-state current	$f = 50\text{ Hz}, I_{GM} = 0.8\text{ A}$ $di_G/dt = 0.8\text{ A}/\mu\text{s}$ $V_D \leq 0.67 V_{DRM}$	300	V/ μs V/ μs V/ μs V/ μs A/ μs

CHARACTERISTICS

Symbols and parameters			Value			Unit
			min	typ	max	
V_T	On-state voltage	$t_{vj} = t_{vj \max}, I_T = 1000 \text{ A}$			1.9	V
$V_{(TO)}$	Threshold voltage	$t_{vj} = t_{vj \max}$	1			V
r_T	Slope resistance	$t_{vj} = t_{vj \max}$	0.7			mΩ
I_{GT}	Gate trigger current	$t_{vj} = 25^\circ\text{C}, v_D = 8 \text{ V}$			200	mA
V_{GT}	Gate trigger voltage	$t_{vj} = 25^\circ\text{C}, v_D = 6 \text{ V}$			2	V
I_{GD}	Gate non-trigger current	$t_{vj} = t_{vj \max}, v_D = 6 \text{ V}$			10	mA
V_{GD}	Gate non-trigger voltage	$t_{vj} = t_{vj \max}, v_D = 0.5 V_{DRM}$			0.25	V
I_H	Holding current	$t_{vj} = 25^\circ\text{C}, v_D = 6 \text{ V}$ $R_A = 5 \Omega$			200	mA
I_L	Latching current	$t_{vj} = 25^\circ\text{C}, v_D = 6 \text{ V}$ $R_{GK} \geq 10 \Omega, I_{GM} = 0.8 \text{ A}$ $di_G/dt = 0.8 \text{ A}/\mu\text{s}$ $t_g = 20 \mu\text{s}$			1	A
i_D, i_R	Forward off-state and reverse current	$t_{vj} = t_{vj \max}$ $v_D = V_{DRM}, v_R = V_{RRM}$			30	mA
t_{gd}	Gate controlled delay time	$t_{vj} = 25^\circ\text{C}, I_{GM} = 0.8 \text{ A}$ $di_G/dt = 0.8 \text{ A}/\mu\text{s}$			1.4	μs
t_q	Turn-off time	See Techn. Inf.			C*: 12 D: 15 E: 20	μs μs μs

THERMAL PARAMETERS

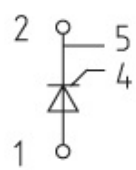
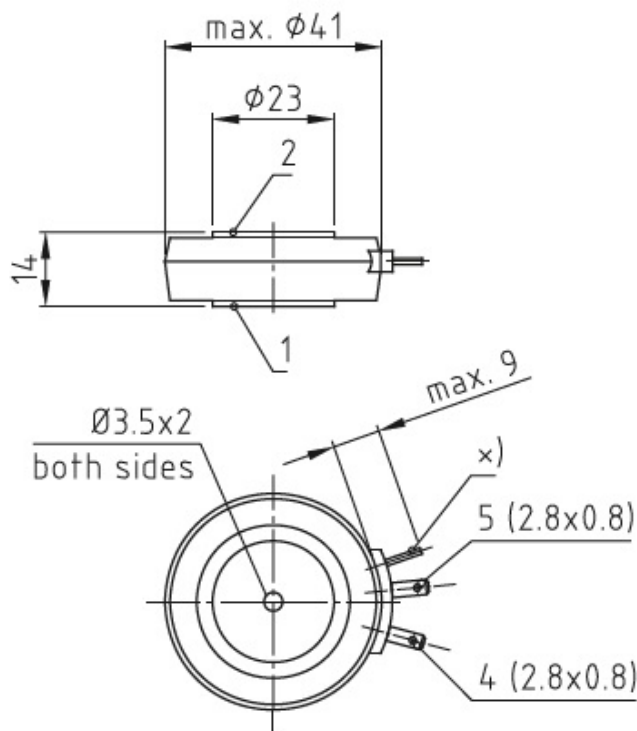
Symbols and parameters			Value	Unit
$R_{th(j-c)}$	Thermal resistance, junction to case	Two-sided cooling, $\theta = 180^\circ$ el, sin Two-sided cooling, DC Anode-sided cooling, $\theta = 180^\circ$ el, sin Anode-sided cooling, DC Cathode-sided cooling, $\theta = 180^\circ$ el, sin Cathode-sided cooling, DC	0.108 0.099 0.189 0.18 0.232 0.22	$^\circ\text{C}/\text{W}$
$R_{th(c-h)}$	Thermal resistance, case to heatsink	Two-sided Single-sided	0.015 0.03	$^\circ\text{C}/\text{W}$
$t_{vj \max}$	Maximum junction temperature		+140	$^\circ\text{C}$
$t_{c \text{ op}}$	Operating temperature range		-40 ... +140	$^\circ\text{C}$
t_{stg}	Storage temperature range		-40 ... +140	$^\circ\text{C}$

MECHANICAL PARAMETERS

Symbols and parameters			Value	Unit
F	Clamping force		2.5 – 5	kN
W	Weight		70	g
D	Creepage distance		17	mm
a	Vibration resistance	f = 50 Hz	50	m/s ²

* - Delivery for larger quantities on request
1) - Values to DIN IEC 747-6 (without prior commutation)
2) - Immediately after circuit commutated turn-off time, see Parameters t_q

DIMENSIONS



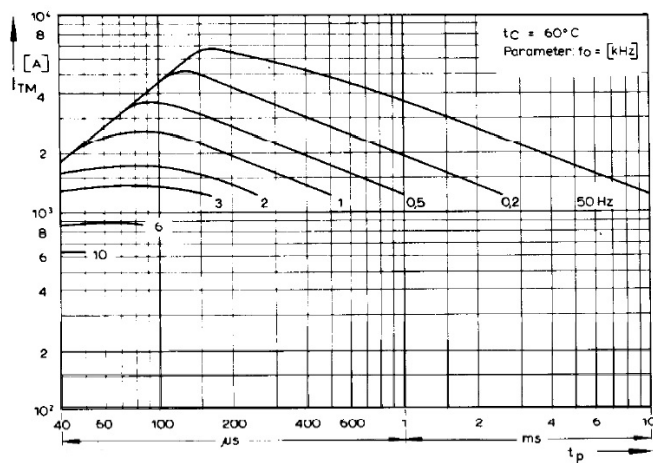


Fig. 1

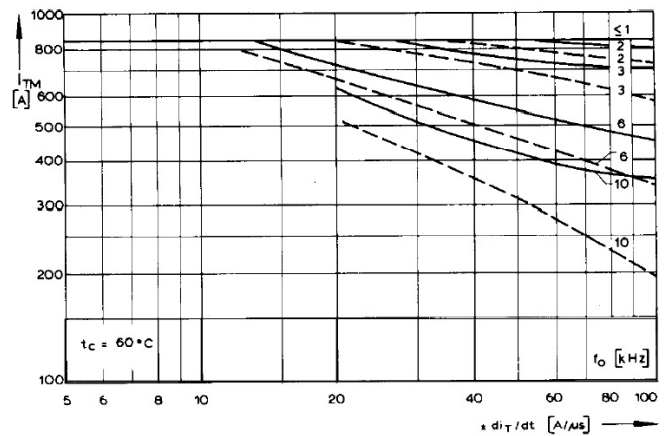


Fig. 4

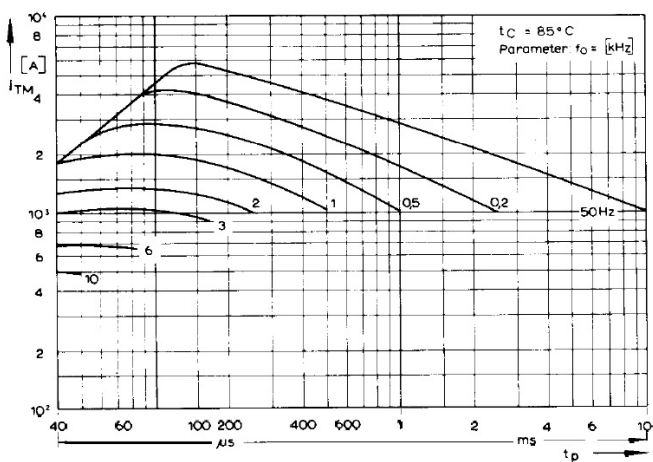


Fig. 2

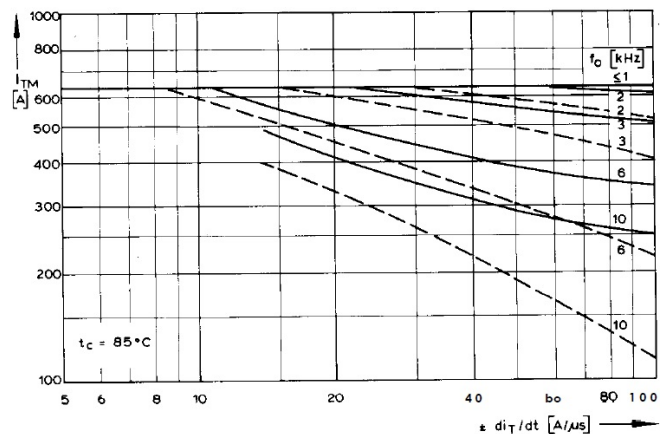


Fig. 5

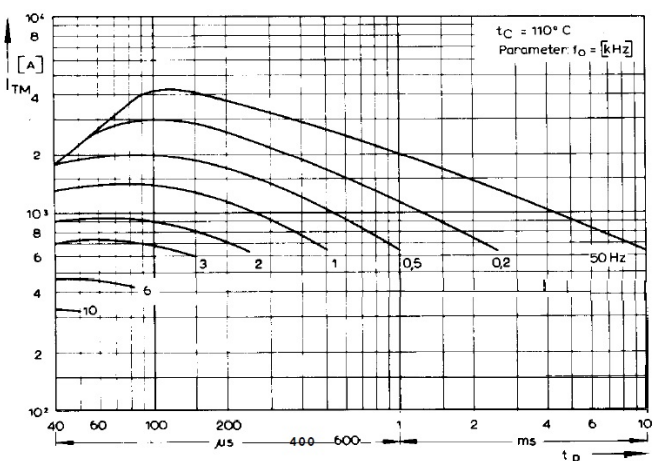


Fig. 3

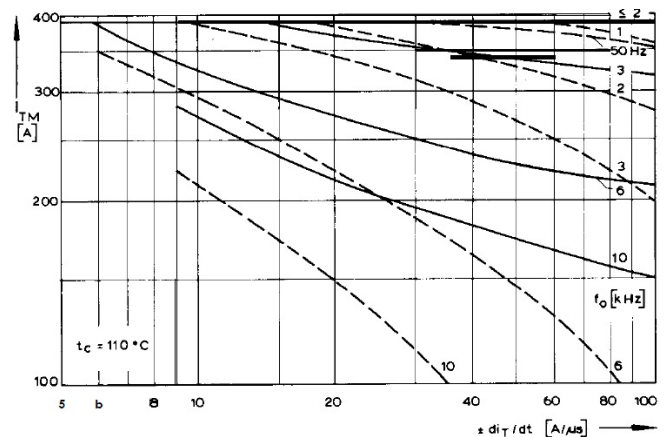


Fig. 6

Fig. 1, 2, 3
Pulse generator:
 $i_G = 0.8 \text{ A}$, $di_G/dt = 0.8 \text{ A}/\mu\text{s}$

RC-network:
 $R [\Omega] \geq 0.02 V_{DM} [V]$
 $C \leq 0.22 \mu\text{F}$
 $V_{DM} \leq 0.67 V_{DRM}$

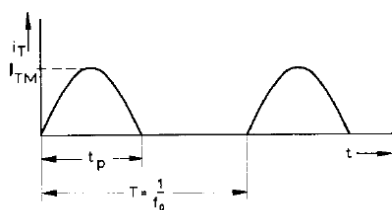
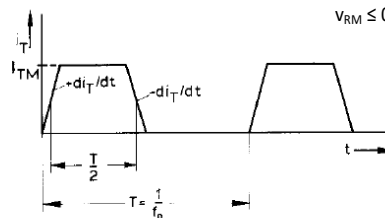


Fig. 4, 5, 6
Pulse generator:
 $i_G = 0.8 \text{ A}$, $di_G/dt = 0.8 \text{ A}/\mu\text{s}$

RC-network:
 $R [\Omega] \geq 0.02 V_{DM} [V]$
 $C \leq 0.33 \mu\text{F}$
 $V_{DM} \leq 0.67 V_{DRM}$
 $dv_R/dt \leq 400 \text{ V}/\mu\text{s}$
 $V_{RM} \leq 0.67 V_{RRM}$



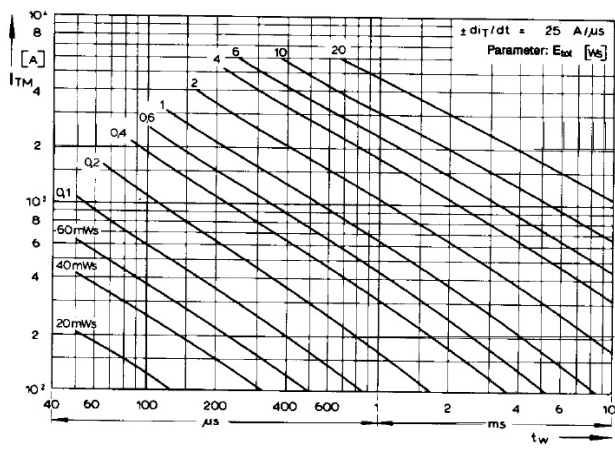


Fig. 7

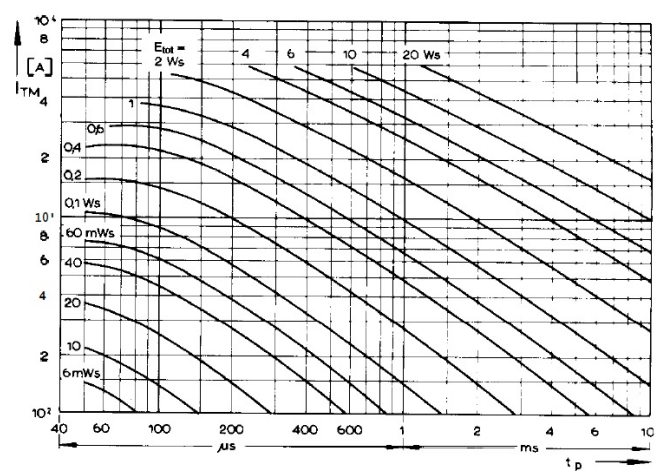


Fig. 10

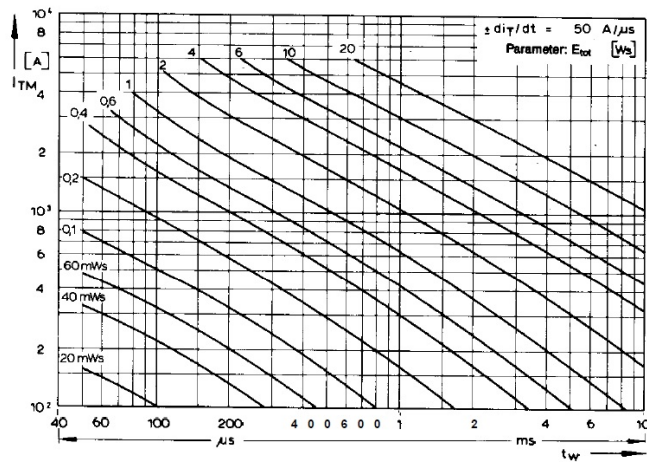


Fig. 8

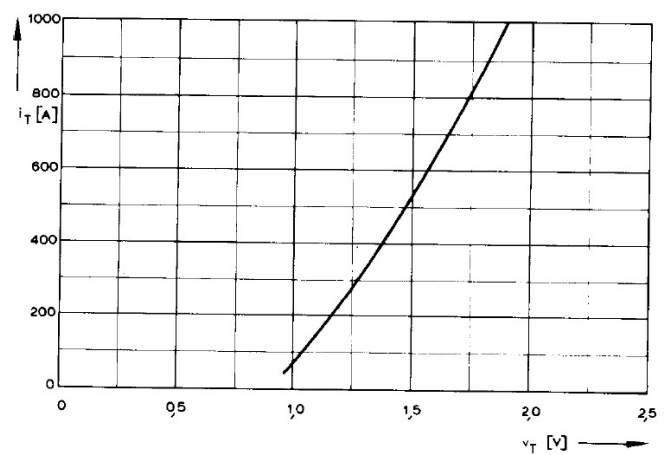


Fig. 11

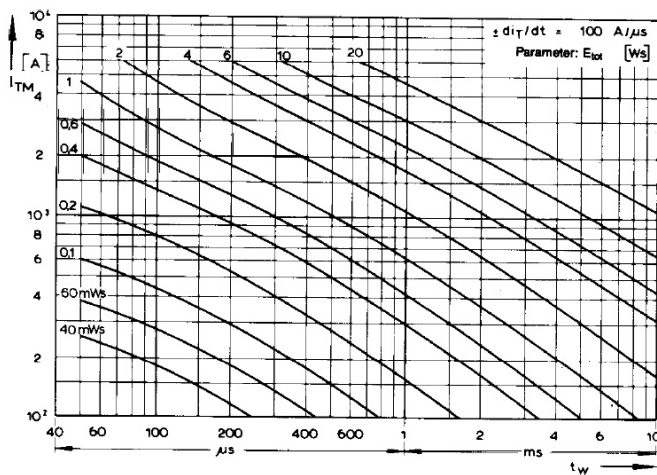


Fig. 9

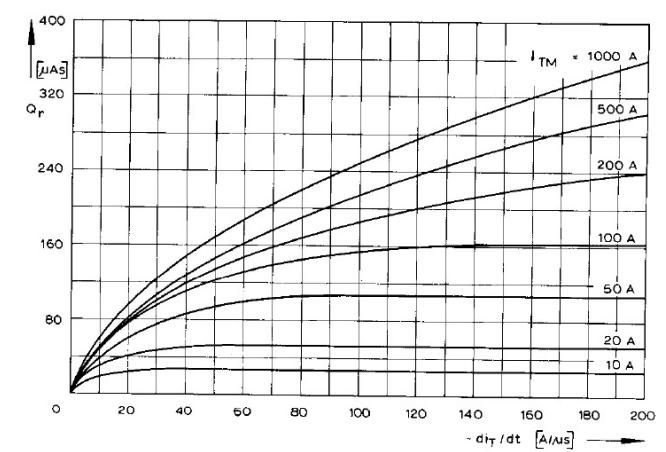


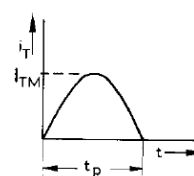
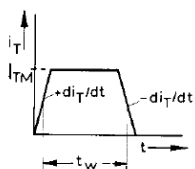
Fig. 12

Fig. 7, 8, 9
Pulse generator:
 $i_G = 0.8 \text{ A}$, $di_G/dt = 0.8 \text{ A}/\mu\text{s}$

RC-network:
 $R [\Omega] \geq 0.02 V_{DM} [V]$
 $C \leq 0.33 \mu\text{F}$
 $V_{DM} \leq 0.67 V_{DRM}$
 $dv_R/dt \leq 400 \text{ V}/\mu\text{s}$
 $V_{RM} \leq 0.67 V_{RRM}$

Fig. 10
Pulse generator:
 $i_G = 0.8 \text{ A}$, $di_G/dt = 0.8 \text{ A}/\mu\text{s}$

RC-network:
 $R [\Omega] \geq 0.02 V_{DM} [V]$
 $C \leq 0.22 \mu\text{F}$



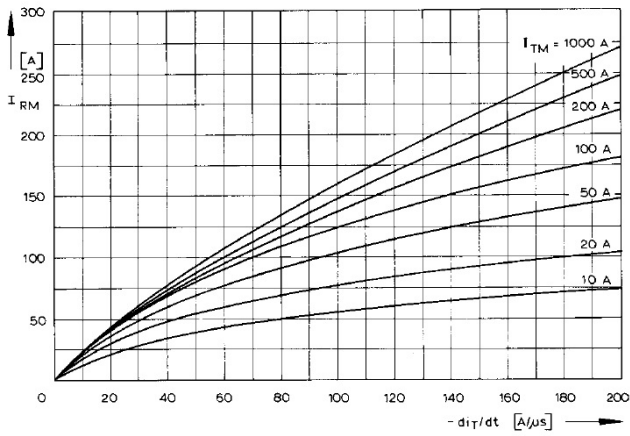


Fig. 13
Peak reverse recovery current
 $I_{RM} = f(-di/dt)$, $t_{vj} = t_{vj(max)}$, $v_R = 0.5 V_{RRM}$, $v_{RM} = 0.8 V_{RRM}$
Parameter: On-state current I_{TM}

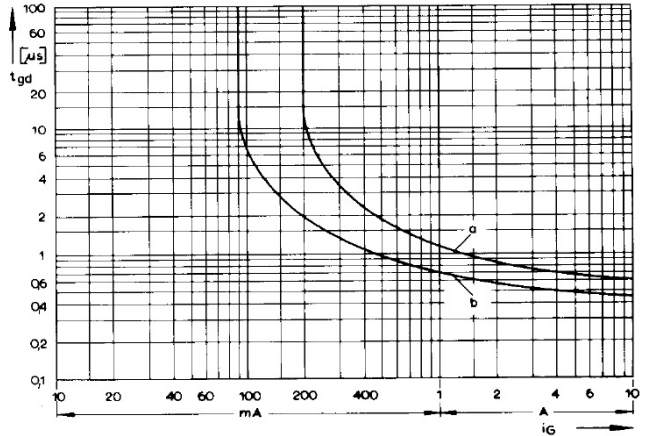


Fig. 15
Gate controlled delay time
 $t_{gd} = f(i_{GM})$, $t_{vj} = 25^\circ\text{C}$, $di_G/dt = i_{GM}/1\mu\text{s}$
a — Limiting characteristic
b — Typical characteristic

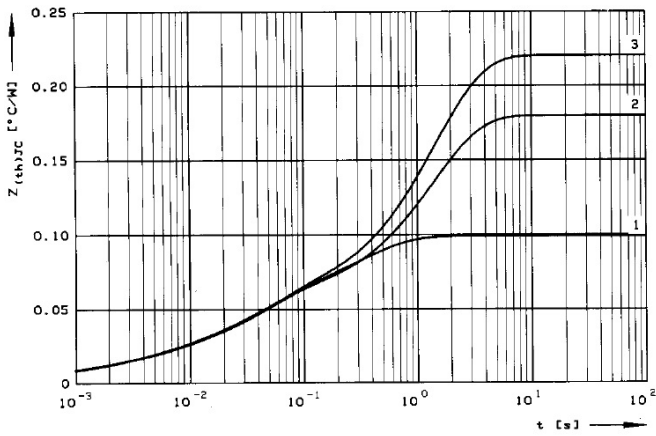


Fig. 14
Transient thermal impedance $Z_{(th)JC} = f(t)$, DC
1 — Two-sided cooling
2 — Anode side cooling
3 — Cathode side cooling

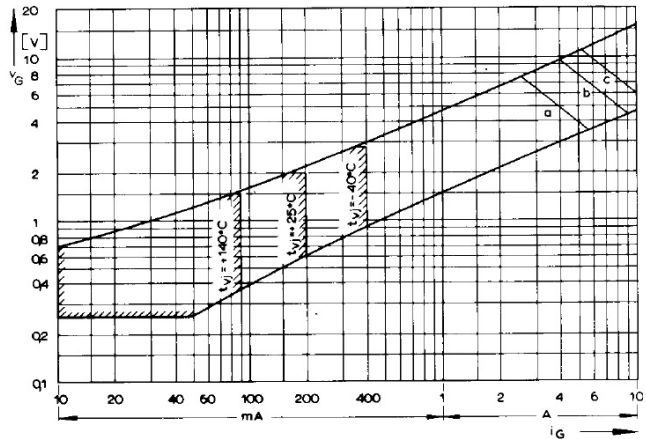


Fig. 16
Gate characteristic with triggering areas $v_G = f(i_G)$, $V_D = 6\text{ V}$
Parameter: Trigger pulse duration t_g [ms]: a - 10; b - 1; c - 0.5
Maximum rated peak gate power dissipation P_{GM} [W]:
a - 20; b - 40; c - 60